

# Effect of synthesis route on the microstructure of SiO<sub>2</sub> doped bismuth titanate ceramics<sup>#</sup>

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## Abstract

Synthesis and characterization of SiO<sub>2</sub> doped bismuth titanate ceramics were investigated. Four investigated compositions belonging to the system  $Bi_2O_3$ -TiO\_2-SiO\_2 are located in the section  $Bi_4Ti_3O_{12}$ -SiO<sub>2</sub>, near by it and in the binary  $Bi_2O_3$ -TiO\_2 system. Melt quenching was applied for synthesis of SiO\_2 doped bismuth titanate ceramics and for the sample  $40Bi_2O_3$ ·60TiO<sub>2</sub>. The binary sample  $70Bi_2O_3$ ·30TiO<sub>2</sub> is prepared by gradient heating of bulk materials near the liquidus temperature (modified solid state reaction). The influence of the thermal treatment on the phase formation and microstructure was evaluated using XRD, EDS and SEM. The binary samples prepared by solid state reaction at low temperature ( $1000^{\circ}C$ ) possess poly-phased dense microstructure, while secondary crystallization combined with porosity formation is typical for the sample obtained at high temperature ( $1150^{\circ}C$ ). The ternary  $Bi_2O_3$ -TiO\_2-SiO\_2 samples, obtained by supercooling of the melts down to room temperature, are thermally treated at 700, 800°C. They consist of elongated crystals in amorphous matrix. The crystals have lower  $Bi_2O_3$ -content and higher TiO\_2-content than the nominal batch composition. The XRD data show that the main crystalline phases in the ceramics produced by melt quenching method and solid state reaction are  $\beta$ -Bi\_2O\_3,  $Bi_4Ti_3O_{12}$  and one unknown new phase. It is proved that the applied methods of synthesis are suitable for generation of different microstructures in the bulk SiO\_2 doped bismuth titanate ceramics, which is promising basis for modification of their electrical properties.

Keywords: bismuth titanate, melt quenching, heat treatment, microstructure

#### I. Introduction

The application of Aurivillius family of bismuthbased ferroelectric compounds with a layered structure [1] in capacitors, sensors, piezoelectric and electrooptic devices [2–4] is strongly influenced by the method of preparation. Doping with different cations is used to control the point defects. Various low- and high-temperature routes of synthesis are used: sol-gel method [5–7], hydrothermal crystallization [8], metal-organic decomposition [9] and others. Recently crystallization from melts and glasses is also applied [10–14]. This method gives possibility to control the particle size evolution during the transition from amorphous to crystalline state and to achieve suitable crystallographic orientation in the polycrystalline materials.

In our previous study, the phase formation in the system  $Bi_2O_3$ - $TiO_2$ - $SiO_2$  from fast quenched melts is investigated [15]. It is established that the introduction of 20–40 mol%  $SiO_2$  stimulates the partial amorphization of the samples. It is known, that the properties of some ferroelectric ceramics can be enhanced by texturing of their structure as in the case of partial grain orientation in polycrystalline  $Bi_4Ti_3O_{12}$  ceramics obtained by sol-gel, magnetic alignment and other methods [16–19]. All these facts motivate our further investigations.

The purpose of the present study is to elucidate the influence of the heat treatment on the phase formation and microstructure of  $SiO_2$  doped bismuth titanate ceramics obtained by melting.

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#### **II. Experimental**

The selection of compositions with high melting temperatures was made according to the data for the liquidus temperature in the system  $Bi_2O_3$ - $TiO_2$  [13,20, 21] as well as to the glass formation in the system  $Bi_2O_3$ -SiO\_2 [22,23]. Four compositions (in mol%) were selected: one in the section  $Bi_4Ti_3O_{12}$ -SiO\_2 (24 $Bi_2O_3$ ·36 $TiO_2$ ·40 $SiO_2$ ), the second near by this area



Figure 1. Gibbs triangle of the system  $Bi_2O_3$ -Ti $O_2SiO_2$  with the selected compositions: 1)  $24Bi_2O_3$ ·36Ti $O_2$ ·40Si $O_2$ ; 2)  $33Bi_2O_3$ ·47Ti $O_2$ ·20Si $O_2$  and 3)  $70Bi_2O_3$ ·30Ti $O_2$ , 4)  $40Bi_2O_3$ ·60Ti $O_2$ 

 $(33Bi_2O_3 \cdot 47TiO_2 \cdot 20SiO_2)$ , and other two in the system  $Bi_2O_3 \cdot TiO_2$  ( $70Bi_2O_3 \cdot 30TiO_2$  and  $40Bi_2O_3 \cdot 60TiO_2$ ) (Fig. 1). The sample having a model binary composition  $70Bi_2O_3 \cdot 30TiO_2$  was prepared with gradient heating of bulk materials near the liquidus temperature (modified solid state reaction) in the temperature range  $1000-1150^{\circ}C$  for 1 hour. The sample with the composition  $40Bi_2O_3 \cdot 60TiO_2$ , corresponding to the phase  $Bi_4Ti_3O_{12}$ , was quenched from melt at  $1300^{\circ}C$ . The three



Figure 2. SEM micrographs of sample with composition 70Bi,O,:30TiO, prepared at: a) 1000°C and b, c) 1150°C



Figure 3. XRD patterns of sample with composition 70Bi<sub>2</sub>O<sub>3</sub>·30TiO<sub>2</sub> prepared at: a) 1000°C and b) 1150°C



40Bi,O,:60TiO, prepared at 1300°C

component samples with SiO<sub>2</sub> were melted in alumina crucibles at 1250°C. The contact between the samples and crucible during the melting was about 15 min. as after longer exposition (3–5 hours) contamination with 3–5 mol%  $Al_2O_3$  was detected. The supercooling of the melts to room temperature was performed by pouring them between two steel plates. Heat treatment was applied at different temperatures in order to obtain crystal-line phases from supercooled samples.

For all samples the phase formation was studied by X-ray diffraction analysis (XRD - TUR M62, Cu-K $\alpha$  radiation) and energy dispersive spectroscopy (EDS - EDAX 9900). The microstructure was observed by scanning electron microscopy (SEM - 525M, Philips). For the EDS analysis the samples were prepared by mechanical polishing and covered with thin carbon film, while the SEM observations were made on fresh fractured surfaces also covered with thin carbon film.

#### **III. Results and discussion**

The investigation started with a model binary composition  $70Bi_2O_3 \cdot 30TiO_2$  obtained by solid state reaction with heating for 1 hour in the temperature range 1000– 1150°C. The SEM analysis illustrates the formation of different microstructures in the sample sintered at lowtemperature, 1000°C (Fig. 2a). Secondary crystallization combined with porosity formation is observed after the high-temperature (1150°C) treatment (Fig. 2b), where clearly shaped cubic-like crystals are formed. The sample prepared at low-temperature is poly-phased one and its XRD data contains the patterns of the phase  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> and some patterns of other non-identified phases (Fig. 3a). The main crystalline phase is  $\beta$ -Bi<sub>2</sub>O<sub>3</sub> (Fig. 3b) for the sample treated at 1150°C.

The sample with composition corresponding to the phase  $Bi_4Ti_3O_{12}$  (40 $Bi_2O_3$ ·60TiO<sub>2</sub>) was quenched from the melt at 1300°C. The XRD analysis shows mainly the formation of the phase  $Bi_4Ti_3O_{12}$  without texturing effects (Fig. 4). The melt quenched sample with composition



Figure 5. SEM micrographs and EDS data of melt quenched sample with composition 24Bi<sub>2</sub>O<sub>3</sub>·36TiO<sub>2</sub>·40SiO<sub>2</sub>: a, b) heat treated at 700°C; c) heat treated at 800°C

 $24\text{Bi}_2\text{O}_3 \cdot 36\text{TiO}_2 \cdot 40\text{SiO}_2$  after subsequent thermal treatment at 700°C, consists of elongated crystals in amorphous matrix (Fig. 5). According to the EDS analysis, the crystals and matrix differ in composition: the crystals have lower Bi<sub>2</sub>O<sub>3</sub>-content and higher TiO<sub>2</sub>-content in comparison to the nominal composition (Figs. 5a,b). For all detected EDS analysis the statistical uncertainty is less than 4–5 mol%. Full crystallization combined with predominating orientation of the crystals is achieved after batch heat treatment for 5 hours at 800°C (Fig. 5c). Before the thermal treatment according to the XRD results,



Figure 6. XRD patterns of sample with composition 24Bi<sub>2</sub>O<sub>3</sub>·36TiO<sub>2</sub>·40SiO<sub>2</sub>: a) without thermal treatment; b) after heating for 5 h at 600°C and for 5 h at 700°C



33Bi<sub>2</sub>O<sub>3</sub>·47TiO<sub>2</sub>·20SiO<sub>2</sub>

the sample was amorphous (Fig. 6a), but after long heating, the crystallization has been achieved (Fig. 6b) and a new phase having XRD patterns close to those of the phase  $Bi_4Ti_3O_{12}$  appears. The decreasing of the  $SiO_2$ -content leads to more complex crystallization with participation of several phases including  $Bi_4Ti_3O_{12}$  and some unknown phase (Fig. 7).

## **IV. Conclusions**

The investigation shows for the first time that depending on the conditions of the melting and additional heat treatment of the supercooled samples, different poly phased ceramic materials with various microstructures could be obtained in the system  $Bi_2O_3$ - $TiO_2$ - $SiO_2$ . Formation of the phase  $Bi_4Ti_3O_{12}$ ,  $Bi_2O_3$ -polymorphs and one unknown phase was established. These results are promising basis for control and modification of the electrical properties of the obtained bulk  $SiO_2$  doped bismuth titanate ceramics.

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